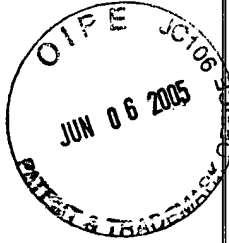


DW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant(s): Zhong Dong et al
Assignee: ProMOS Technologies Inc.
Title: Method of Forming ONO-Type Sidewall with Reduced Bird's Beak
Serial No.: 10/821,100 Filing Date: April 7, 2004
Examiner: Vu, David Group Art Unit: 2818
Docket No.: M-15295 US

San Jose, California
June 02, 2005

**COMMISSIONER FOR PATENTS
P.O. BOX 1450
ALEXANDRIA, VA 22313-1450**

RESPONSE TO RESTRICTION, WITH TRAVERSE

Dear Sir:

In response to the Office Action having a mailing date of May 16, 2005, Applicant hereby provisionally elects Group II (method claims 1-15) with traverse.

REMARKS

Device Claim 16 (Group I) recites: "a sidewall-coating dielectric whose fabrication was at least initially started by subjecting at least one otherwise exposed and multi-layered sidewall of the ONO-type memory cell stack to a dry ISSG process (In-Situ Steam Generation)." (Emphasis added.)

The basis of restriction argues that "for example, the sidewall dielectric could be formed on an ONO stack by CVD rather than ISSG process." (OA page 2, 6th line from bottom).

MacPherson Kwok Chen & Heid
J.L.P.
1762 Technology Drive,
Suite 226
San Jose, CA 95110
Telephone: (408) 392-9250
Facsimile: (408) 392-9262